COS/MOS Analog Multipl xers/Demultiplexers*

With Logic-Level Conversion

High-Voltages Types (20-Volt Rating)

CD4051B — Single 8-Channel CD4052B — Differential 4-Channel CD4053B — Triple 2-Channel

RCA-CD4051B, CD4052B, and CD4053B analog multiplexers/demultiplexers are digitally controlled analog switches having low ON impedance and very low OFF leakage current. Control of analog signals up to 20 V peak-to-peak can be achieved by digital signal amplitudes of 4.5 to 20 V (if VDD-VSS = 3 V, a VDD-VEE of up to 13 V can be controlled, for VDD-VEE level differences above 13 V, a VDD-VSS of at least 4.5 V is required). For example, if V_{DD} = +4.5 V, V_{SS} = 0, and V_{EE} = -13.5 V, analog signals from -13.5 V to +4.5 V can be controlled by digital inputs of 0 to 5 V. These multiplexer circuits dissipate extremely low quiescent power over the full VDD-VSS and VDD-VEE supply-voltage ranges, independent of the logic state of the control signals. When a logic "1" is present at the inhibit input terminal all channels are off.

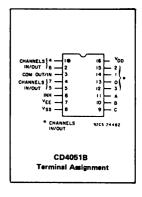
The CD4051B is a single 8-channel multiplexer having three binary control inputs, A, B, and C, and an inhibit input. The three binary signals select 1 of 8 channels to be turned on, and connect one of the 8 inputs to the output.

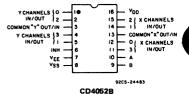
The CD4052B s a differential 4-channel multiplexer having two binary control inputs, A and B, and an inhibit input. The two binary input signals select 1 of 4 pairs of channels to be turned on and connect the analog inputs to the outputs.

The CD4053B is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a singlepole double-throw configuration.

The CD4051B, CD4052B, and CD4053B are supplied in 16-lead ceramic dual-in-line packages (D and F suffixes), 16-lead plastic dual-in-line packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix). Applications:

- Analog and digital multiplexing and demultiplexing
 A/D and D/A conversion
 Signal gating
- Features:
- Wide range of digital and analog signal levels: digital 3 to 20 V, analog to 20 V_{D-D}
- Low ON resistance: 125 Ω (typ.) over 15
 V_{p-p} signal-input range for VDD-VEE = 15 V
- High OFF resistance: channel leakage of ±100 pA (typ.) @ V_{DD}-V_{EE} = 18 V
- Logic-level conversion for digital addressing signals of 3 to 20 V (VDD-VSS = 3 to 20 V) to switch analog signals to 20 V p-p (VDD-VEE = 20 V); see introductory text
- Matched switch characteristics: RON = 5 Ω (typ.) for VDD-VEE = 15 V
- Very low quiescent power dissipation under under all digital-control input and supply conditions: 0.2 µW (typ.) @ VDD-VSS = VDD-VEE = 10 V
- Binary address decoding on chip
- 5-, 10-, and 15-V parametric ratings
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C





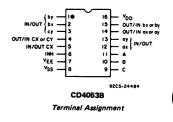


RECOMMENDED OPERATING CONDITIONS AT T_A = 25°C (Unless Otherwise Specified)

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges. Values shown apply to all types except as noted.

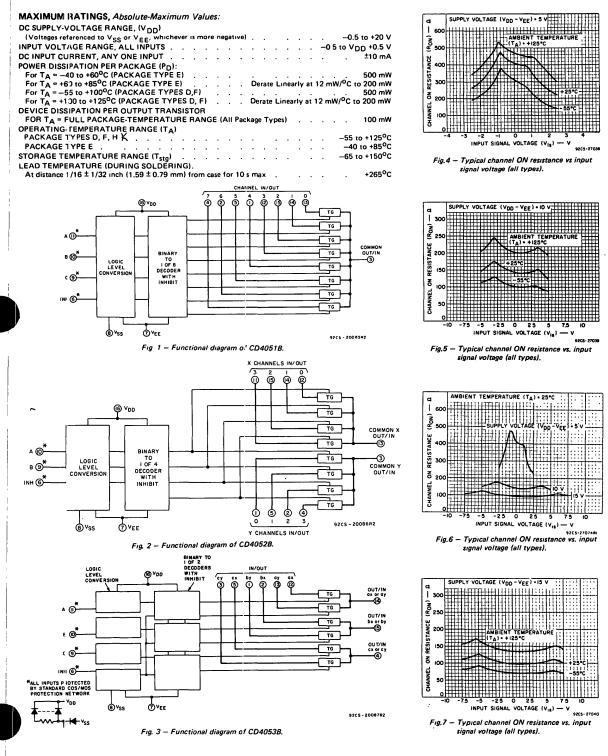
CHARACTERISTIC	VDD	Min.	Max.	Units
Supply-Voltage Range (T _A = Full Package- Temp. Range)	-	3	18	v
Multiplexer Switch Input Current Capability*	_	-	25	mA
Output Load Resistance	-	100	-	Ω

In certain applications, the external load-resistor current may include both VDD and signal-line components. To avoid drawing VDD current when switch current flows into the transmission gate inputs, the voltage drop across the bid rectional switch must not exceed 0.8 volt (calculated from RQN values shown in ELECTRICAL CHARACTERISTICS CHART). No VDD current will flow through RL if the switch current flows into terminal 3 on the CD4051; terminals 3 and 13 on the CD4053.



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^{*} When these devices are used as demultiplexers, the "CHANNEL IN/OUT" terminals are the outputs and the "COMMON OUT/IN" terminals are the inputs.



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ELECTRICAL CHARACTERISTICS

CHARAC-	V _{is}		V _{DD}	LIMITS at Indicated Temperature (°C) Values at -55,+25,+125, apply to D,F,H pkg Values at -40,+25,+85, apply to E pkgs						14-1-1						
TERISTIC	(V)	(V)	v _{ss} (v)	(V)	55	-40	+85	+125	+25			Units				
					-55		100	125	Min.	Тур.	Max.					
SIGNAL INPUTS	(Vis) A	ND OU	TPUTS	(Vos	;)											
Quiescent Device			<u> </u>	5	5	5	150	150	_	0.04	5	μA				
Current, IDD				10	10	10	300	300	-	0.04	10	1				
Max.				15	20	20	600	600	-	0.04	20					
				20	100	100	3000	3000		0.08	100					
On-State																
Resistance	[[1		í –											
o≤v _{is} ≤v _{DD}		0	0	5	800	850		1300	-	470	1050					
r _{on} Max.		0	0	10	310	330	520	550	-	180	400	Ω				
		0	0	15	200	210	300	320		125	240	+				
Change in On																
State Resistance (Between Any		{														
Two Channels)		0	0	5						15						
Δ r _{on}		0	0	10		-	-			10		Ω				
	<u> </u>	1 õ	10	15	<u> </u>	<u> </u>			-	5						
OFF Channel	<u> </u>	<u>├</u> ──	<u> </u>													
Leakage Current:	1				ł						1					
°		1														
Any Channel		1														
OFF Max.	1	0	0	18) ±1	00*	±10	00*	-	±'0.01	±100*	nA				
All Channels				[
OFF (Common]	1													
OUT/IN) Max.					[l					
Capacitance:																
Input, C _{is}	1					-	-	-		5	-					
Output, Cos																
CD4051				1	<u> </u>	-				30	-	pF				
CD 4052 CD 4053		-5	-5	5	<u> </u>					18		Į				
	1		ļ	l			-			9	-	{				
					-	-	-	-	-	02	-					
Feedthrough, Cios		L	L		<u>├</u> ───											
Cios																
C _{ios} Propagation Delay												1				
C _{ios} Propagation Delay Time (Signal In-		R,'= 2	00 kΩ	5	_	_	_	_		30	60					
C _{ios} Propagation Delay		RL'= 2 Ci =	00 kΩ 50 pF	5	-	-	-		-	30 15	60 30	ns				

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* Determined by minimum feasible leakage measurement for automatic testing.

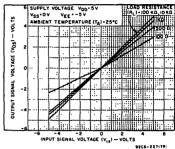


Fig.8 – Typical ON characteristics for 1 of 8 channels (CD4051B).

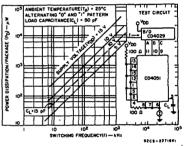
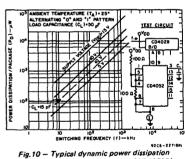
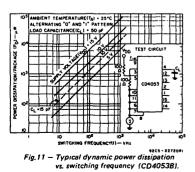


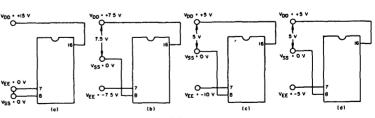
Fig.9 - Typical dynamic power dissipation vs. switching frequency (CD4051B).



 Typical dynamic power dissipation vs. switching frequency (CD4052B).

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The ADDRESS (digital-control inputs) and INHIBIT logic levels are: "O" = V_{SS} and "1" = V_{DD}. The analog signal (through the TG) may swing from V_{EE} to V_{DD}.

Fig. 12 - Typical bias voltages.

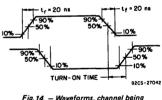
ELECTRICAL CHARACTERISTICS (Cont'd)

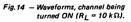
	с	LIMITS at Indicated Temperature (^o C) Values at£i5,+25,+125, apply to D,F,H pkg										
CHARAC- TERISVIC	V _{is}	VEE	VSS	VDD	Values at -40,+25,+85, apply to E pkgs							Units
	(V)	(V)	(v)	(V)	55	_40	+85	+125		+25		Units
						-40	+60	+125	Min.	Тур.	Max.	
CONTROL (ADD	RESS o	r INHIE	BIT) V	с								
Input Low Voltage, VIL												
Max.		VEE=	VSS	5		1	.5		-	_	1.5	
	=VDD	RL=1	kΩ	10			3		_	-	3	
	thru 1 kΩ	to V		15					-		4	l v l
Input High	1 832	us<		5	ļ	3			3.5	-		l * I
Voltage, V _{IH}		on all	OFF	10			7		7	-	-	
Min.		Chann	15		1	1	·	11	-	_		
Input Current, I _{IN} Max.	V _{IN} = 0,18 18				±0.1	±0.1	±1	±1	-	±10-5	±0.1	μΑ
Propagation Delay Tirne:	t _r ,t _f = 2	20 ns, C	L = 50	рF								
Address-to-		0	0	5	1_	-	_	-	_	360	720	
Signal OUT		ō	0	10	<u> </u>		-	- 1	_	160	320	
(Channel: ON or OFF) See		0	0	15	-		-	1 -	-	120	240	ns
Figs.14,15,18		5	0	5	-	-	-	-	-	225	450	
	$R_{1} = 10$	kΩ, C	=50	ъF	1	<u>├</u> ──-		<u> </u>				
	t _r , t _f =											
Inhibit-to-		0	0	5	1_	-	-	-	_	360	720	
Signal OUT		0	0	10	- 1	_	-	-	-	160	320	ns
(Channel turn-		0	0	15	-	-	-	-	-	120	240	115
ing ON)		-10	0	5	-	-	-	-	-	200	400	
	RL=30 t _r ,tf =	0Ω,CL 20 ns	=50 p	F								
Inhibit-to-	ļ	0	0	5	1 -			-		200	450	
Signal OJT	1	0	0	10		-	-	-	-	90	210	ns
(Channel turn-		0	0	15	-		-	=	-	70	160	
ing OFF)	L	-10	0	5	-	-	-		-	130	300	
Input Capacitance, C _{IN} (Any Address or Inhibit Input)					-	-	-	_	-	5	7.5	pF

INPUT S	TA	TE	S	"ON" CHANNEL(S)					
INHIBIT	С	В	A	"ON" CHANNEL(S)					
CD4051B									
0	0	0	0	0					
0	0	0	1	1					
0	0	1	0	2					
0	0	1	1	3					
0	1	0	0	4					
0	1	0	1	5					
0	1	1	0	6					
0	1	1	1	7					
1	X	X	х	NONE					
CD4052B									
INHIBIT		B	Α						
0		0	0	0x, 0y					
0		0	1	1x, ly					
0		1	0	2x, 2y					
0		1	1	Зх, Зу					
1		X	Х	NONE					
CD4053B									
INHIBIT	A or B or C								
0		0		ax or bx or cx					
	T	1		ay or by or cy					
0	1								

X = Don't care

Fig. 13 - Truth tables.





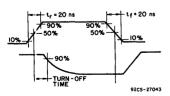
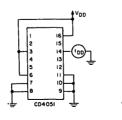


Fig. 15 - Waveforms, channel being turned OFF ($R_L = 300 \ \Omega$).



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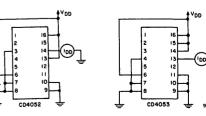


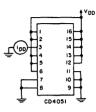
Fig. 16 - OFF channel leakage current - any channel OFF.

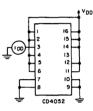
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ELECTRICAL CHARACTERISTICS (Cont'd)

			LIMITS						
CHARACTERISTIC	V _{is} (V)	V _{DD} (V)	RL (kΩ)				TYPICAL VALUE	UNITS	
Cutoff (-3-dB)	5 •	10	1			CD4053	30		
Frequency	VEE = VSS,		V _{os} at Co	ommon OUT/IN	CD4052	25	MHz		
Channel ON (Sine Wave Input)	$20\log\frac{V_{OS}}{V_{IS}} = -3dB$				CD4051	20			
(Sille Wave input)			V _{OS} at A	ny Channel		60			
	2•	5					0.3		
Total Harmonic	3•	10	10				0.2		
Distortion,	5●	15					0.12	%	
тнр	VEE = VSS,								
	f _{is} = 1 kHz sine wave								
-40-dB Feedthrough	5●	10	1			CD4053	8		
	$V_{EE} = V_{SS},$ $20 \log \frac{V_{OS}}{V_{IS}} = -40 dB$			Vos at Common OUT/IN		CD4052	10	MHz	
Frequency					CD4051	12			
(All Channels OFF)			=~40dB	V _{OS} at Any Channel			8		
				Between	Any 2 Channels		3		
			,	Between Measured on Common		mmon	6		
-40-dB Signal Crosstalk Frequency	VEE	5• 10 VEE = V _{SS} ,		Sections CD4052 Only	Measured on An Channel	ער 10			
	$20\log \frac{V_{os}}{V_{is}} = -40 dB$		=40dB	Between Any 2	In Pin 2, Out Pin 14		25	MHz	
			Sections CD4053 Only	In Pin 15, Out F	Pin 14	6			
Address-or-Inhibit- to Signal Crosstalk	= 20 ns	, VC =	10# 0, t _r ,t _f VDD Wave)				65	mV (Peak)	

TEST CIRCUITS (Cont'd)





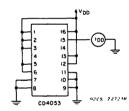
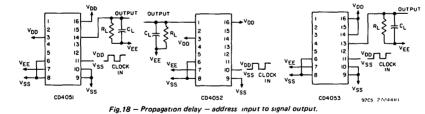


Fig.17 — OFF channel leakage current — all channels OFF.

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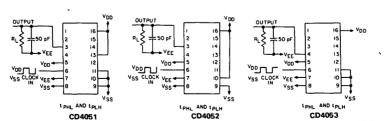
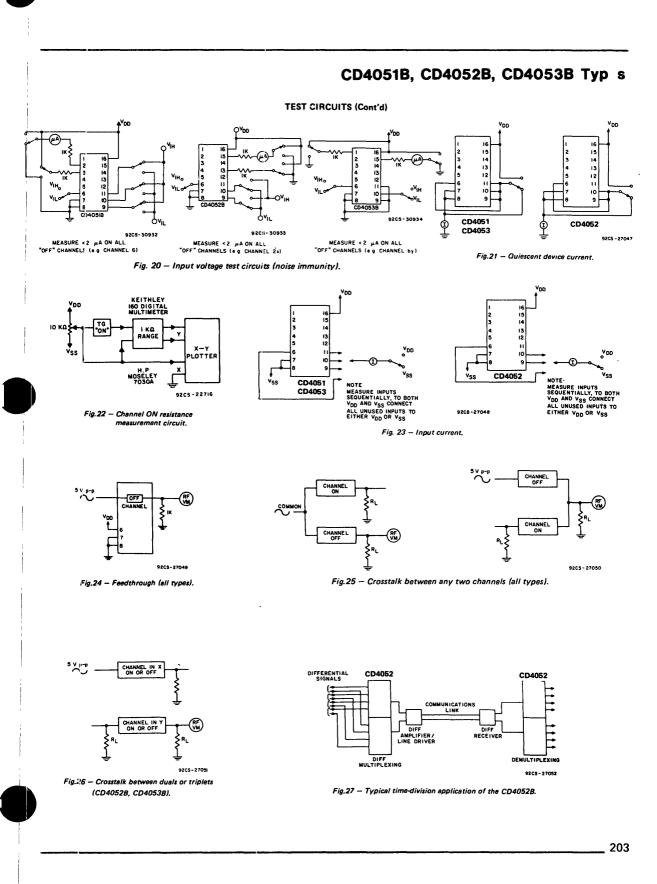


Fig. 19 - Propagation delay - inhibit input to signal output.

Peak-to-peak voltage symmetrical about VDD - VEE
 2

Both ends of channel

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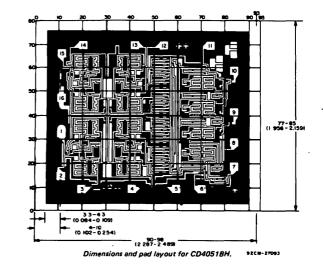


SPECIAL CONSIDERATIONS

In applications where separate power sources are used to drive VDD and the signal inputs, the VDD current capability should exceed VDD/RL (RL = effective external load). This provision avoids permanent current flow or clamp action on the VDD supply when power is applied or removed from the CD40518, CD40528, or CD40538.

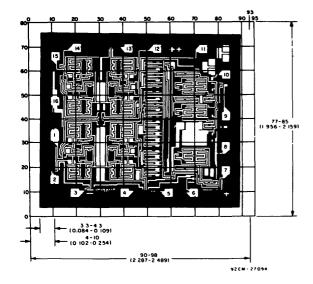
When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned ON or OFF by an address input, there is a momentary conductive path from the channel to VEE, which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning ON a channel will similarly dump some charge to VEE.

The amount of charge dumped is mostly a function of the signal level above VEE. Typically, at VDD-VEE = 10 V, a 100 pF capacitor connected to the input or output of the channel will lose 3-4 % of its voltage at the moment the channel turns ON or OFF. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1-2 When the inhibit signal turns a channel ШS. OFF, there is no charge dumping to VEE. Rather, there is a slight rise in the channel voltage level (65 mV typ.) due to capacitive coupling from inhibit input to channel input or output. Address inputs also couple some voltage steps onto the channel signal levels.

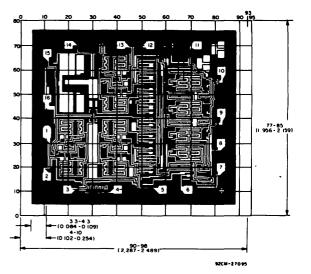


The photographs and dimensions of each COS/MOS chip represent a chip when it is part of the wafer. When the wafer is cut into chips, the cleavage angles are 57° instead of 90° with respect to the face of the chip. Therefore, the isolated chip is actually 7 mils (0 17 mm) larger in both dimensions.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid Graduations are in Mils (10^{-3} inch) .



Dimensions and pad layout for CD4052BH.



Dimensions and pad layout for CD4053BH.